



Variation-Aware Modeling Method for MRAM Behavior Model using System-Verilog

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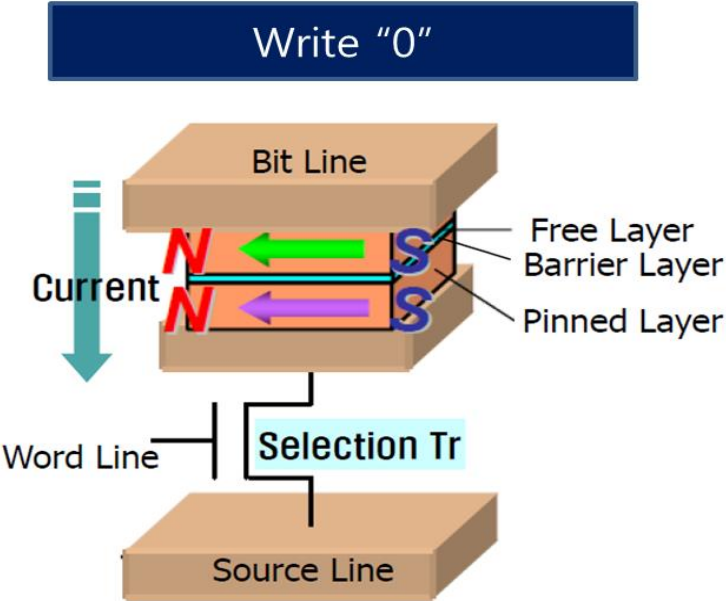
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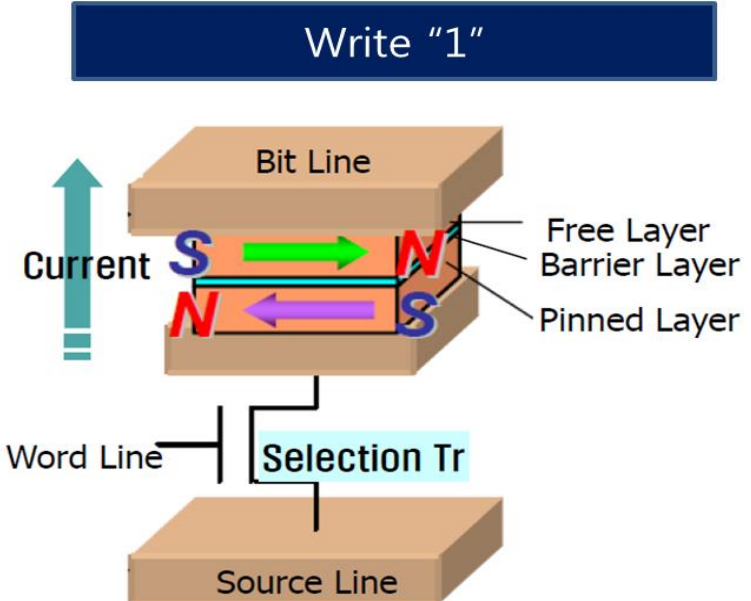
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MRAM Bit-cell



Electrons flow from pinned layer to free layer.
→ Low Resistance state



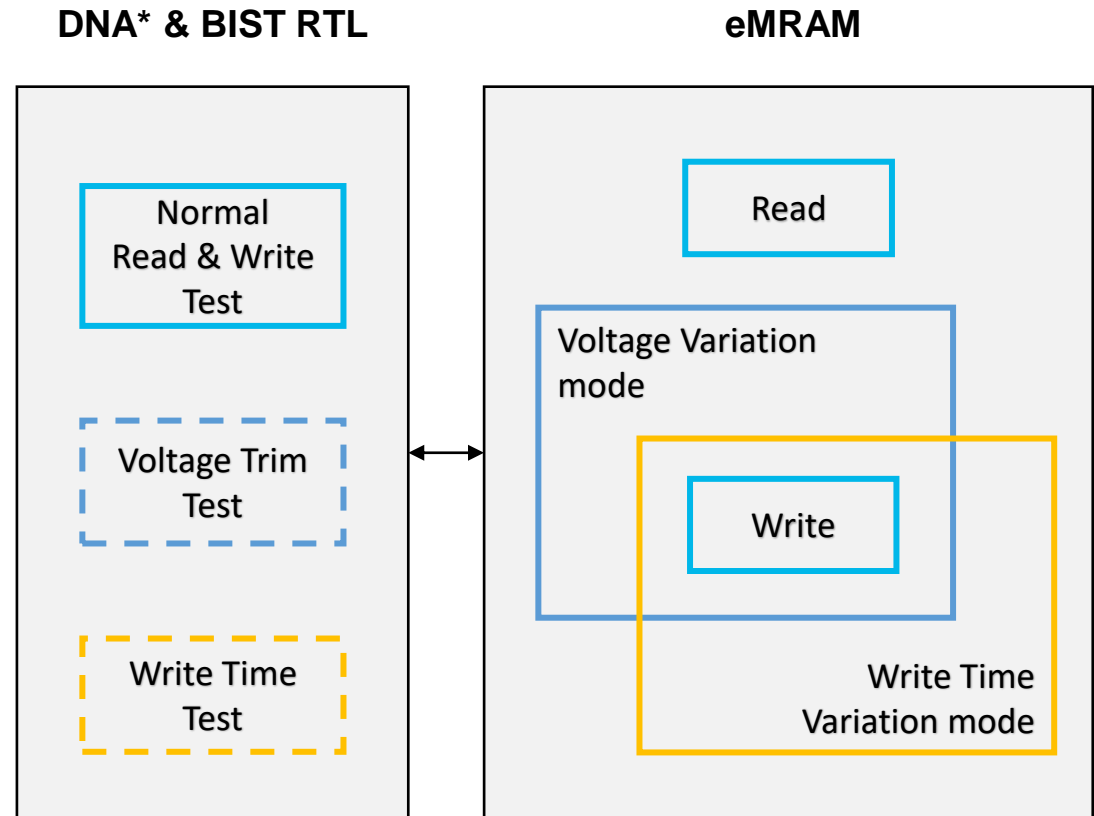
Electrons flow from free layer to pinned layer.
→ High Resistance state

Special Characteristics of Write Possibility

- Time Depend Possibility
 - Single Write Operation does not guarantee write operation
 - Probabilistic write operation modeling does not guarantee exact write operation for simulation.
 - After write guarantee specification time, write should be guarantee.
- Voltage Depend Possibility
 - Reference voltage characteristic is individual properties for each MRAM bit-cell.
 - Voltage characteristic follow the process variation.
 - If write failed, saved data could be reserve or inversed or crashed.

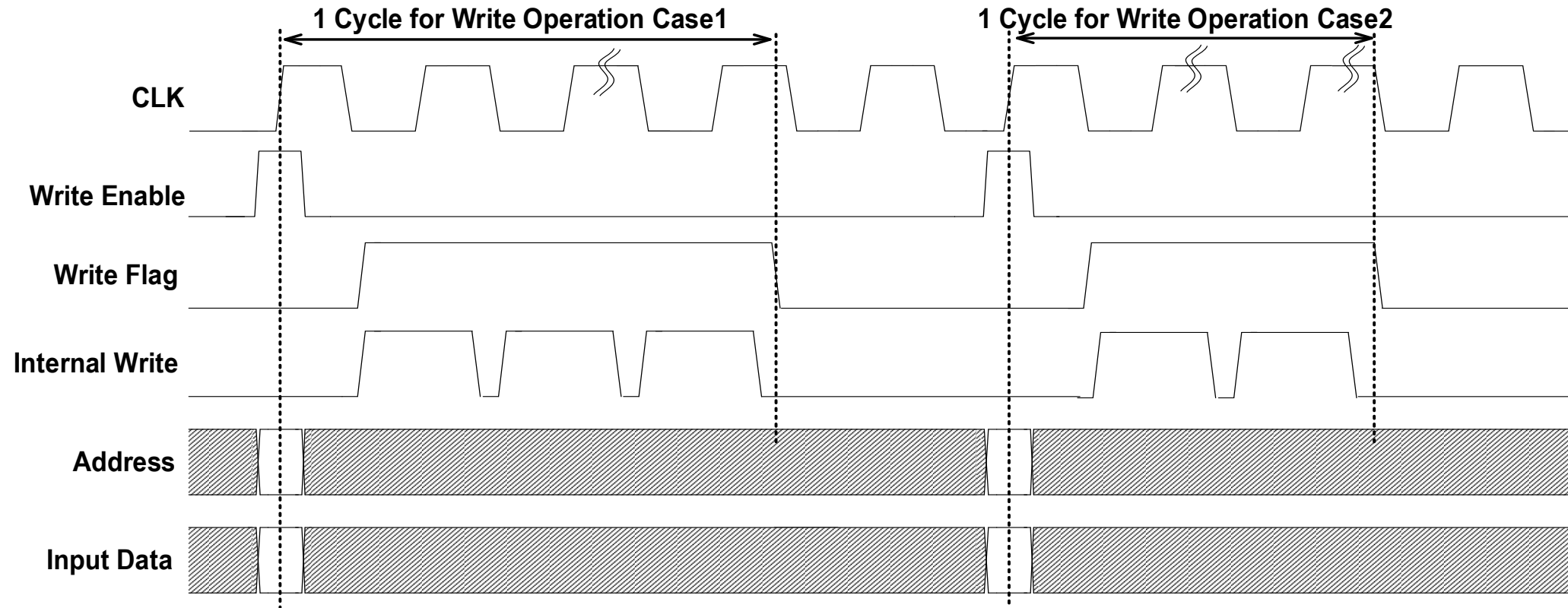
Why need & Where to use ?

- Enables Design Verification for BIST RTL
 - For Memory BIST, commercial tool does not support MRAM
 - MRAM use custom BIST RTL to verify the memory operation
 - Probabilistic MRAM model support verification of the DNA RTL & custom BIST RTL.

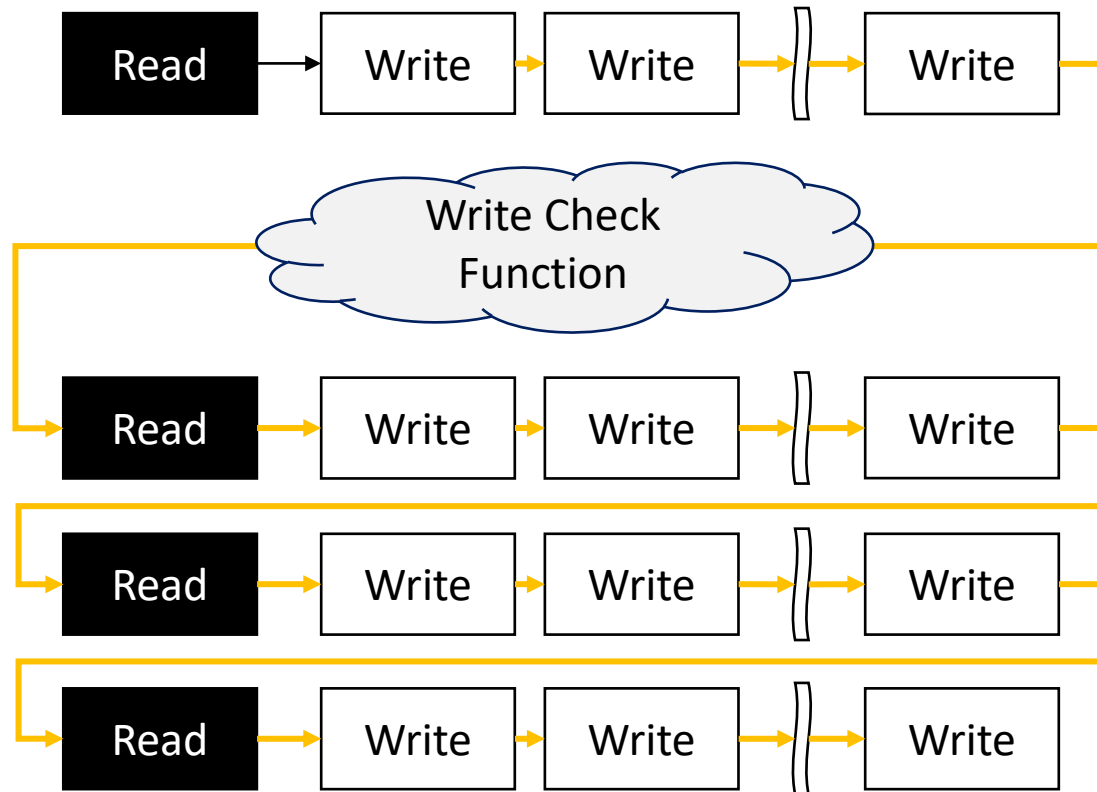


DNA* : Digital Non-volatile Assist

Write Operation Timing Diagram



Write Possibility Modeling

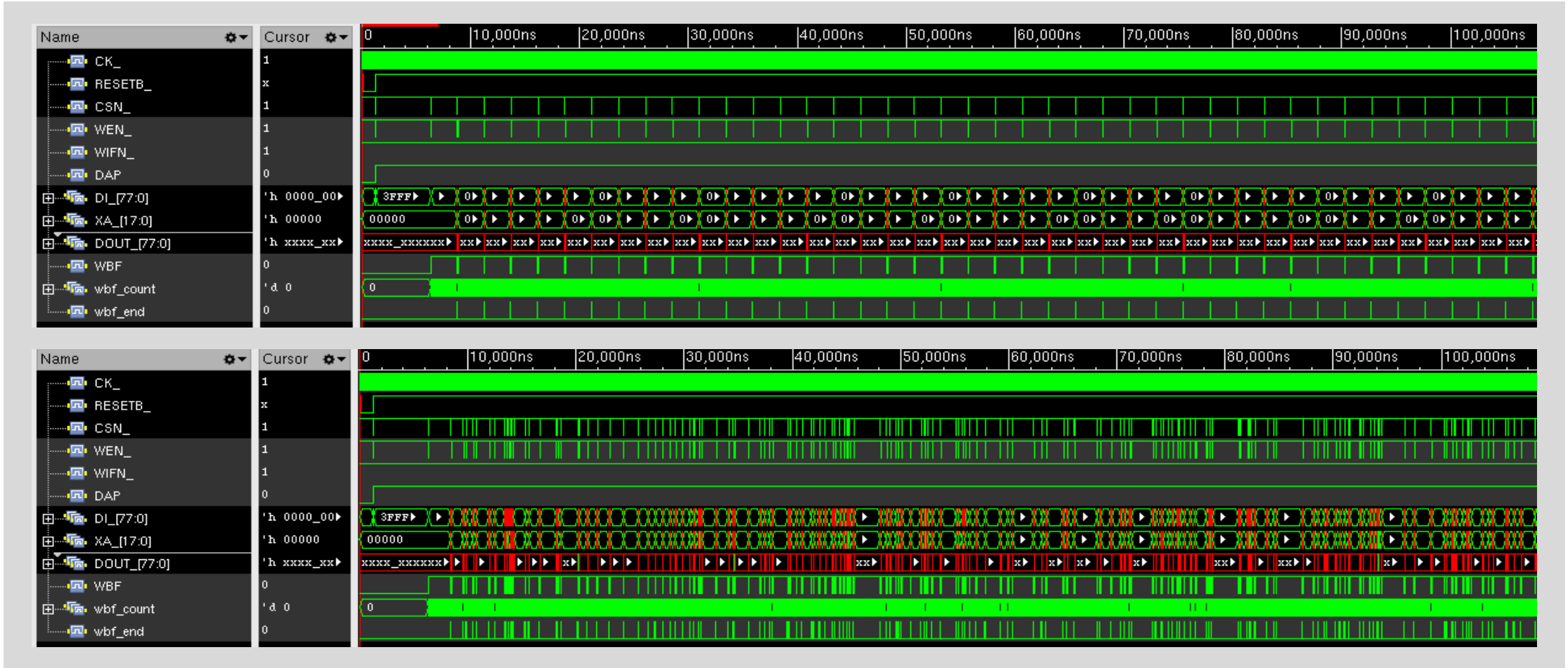


Verilog modeling code

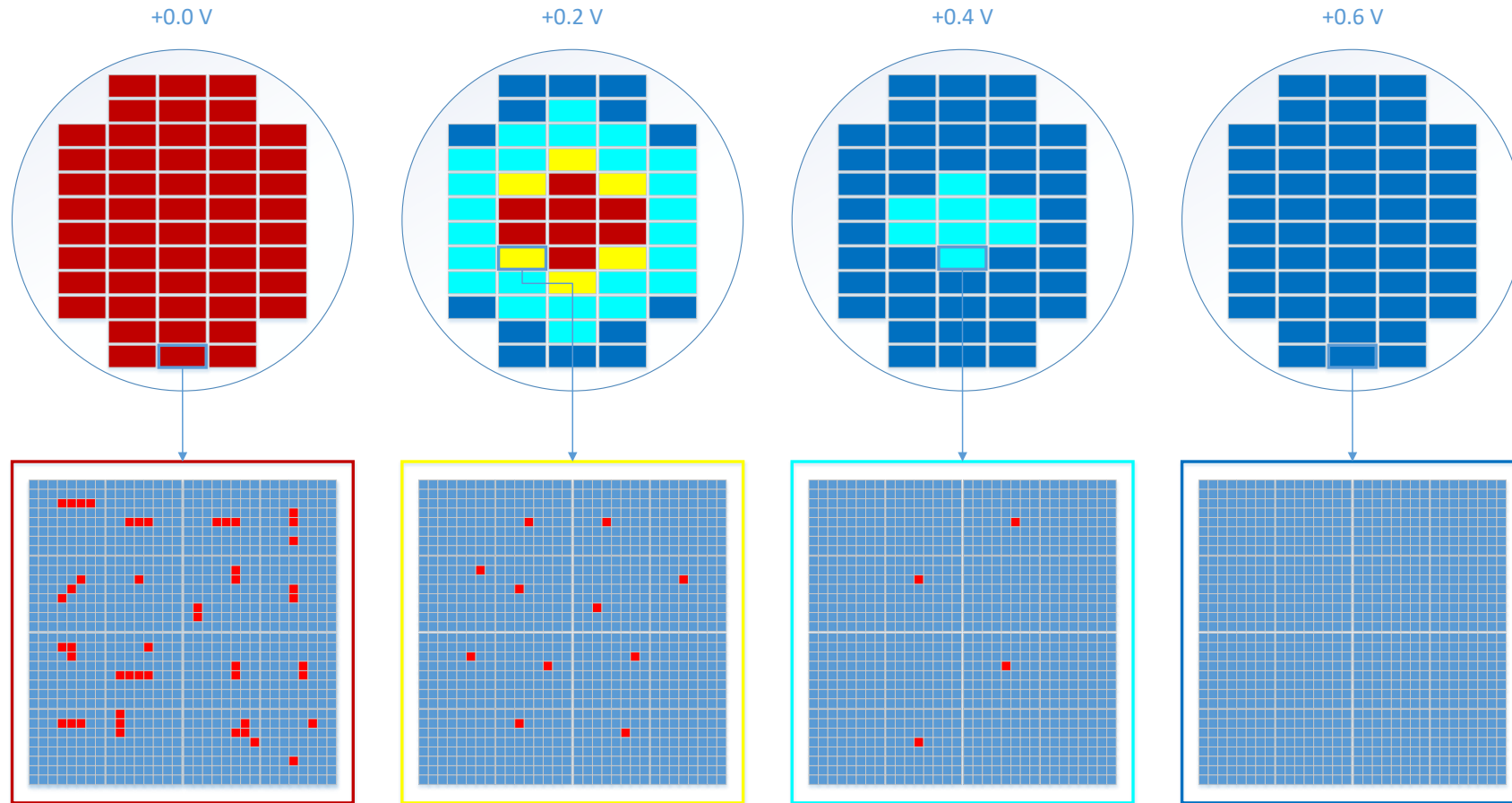
- Decide write pass for every single internal write operation.
- Decision is occur between WBF min/max spec.
- Independent for bit-cell location or address

```
// =====  
// Write Time Variation Modeling  
// =====  
'ifdef WBF_RANDOM  
|---reg [6:0] rand_seed;  
|---always @(ck_negedge) begin: wbf_random  
|---|---rand_seed = $urandom_range(0,100);  
|---|---if ( WBF_reg == 1'b1 ) begin  
|---|---|---if ( rand_seed < █ & wbf_count > 1 ) begin  
|---|---|---|---disable wbf_cycle;  
|---|---|---|---wbf_end = 1'b1;  
|---|---|---end  
|---|---end  
|---end  
'endif
```


Simulation Result

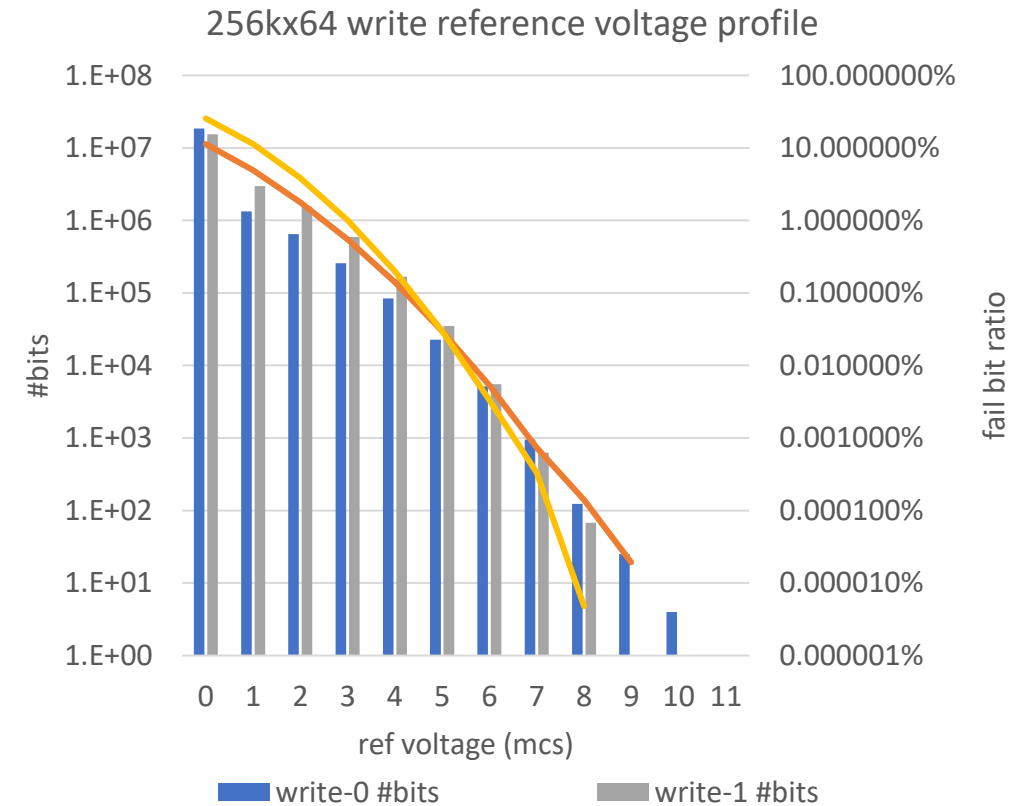


How Voltage Variation Effects Yield



Write Voltage Trimming Configuration

Write-0 Trim-Level	FAIL Ratio	Failure bit-cell # (ideal)		Write-1 Trim-Level	FAIL Ratio	Failure bit-cell # (ideal)	
		16Mb	128Mb			16Mb	128Mb
0	21.83500%	3,663,305	29,306,443	0	45.57641%	7,646,453	61,171,625
1	11.08118%	1,859,114	14,872,908	1	25.24925%	4,236,122	33,888,975
2	4.77904%	801,789	6,414,313	2	11.08118%	1,859,114	14,872,908
3	1.73814%	291,611	2,332,890	3	3.77202%	632,840	5,062,717
4	0.53009%	88,935	711,478	4	0.98153%	164,674	1,317,391
5	0.13499%	22,648	181,180	5	0.19330%	32,431	259,447
6	0.02861%	4,800	38,402	6	0.02861%	4,800	38,402
7	0.00504%	845	6,758	7	0.00317%	531	4,251
8	0.00073%	123	986	8	0.00026%	44	351
9	0.00009%	15	119	9	0.00002%	3	21
10	0.00001%	1	12	10	0.00000%	0	1
11	0.00000%	0	1	11	0.00000%	0	0
12	0.00000%	0	0	12	0.00000%	0	0
13	0.00000%	0	0	13	0.00000%	0	0
14	0.00000%	0	0	14	0.00000%	0	0
15	0.00000%	0	0	15	0.00000%	0	0



Bit-Cell Modeling Technique

- Previous MRAM bit-cell Array modeling

```
|---// Memory definition-  
|---reg [(word_width+r_col*0)*mux-1:0] mem[0:4095];  
|---reg [(word_width+r_col*0)*mux-1:0] mem0[0:3];  
|---reg [(word_width+r_col*0)*mux-1:0] mem1[0:3];  
|---reg [(word_width+r_col*0)*mux-1:0] mem2[0:3];  
|---reg [(word_width+r_col*0)*mux-1:0] mem3[0:3];  
|---reg [(word_width+r_col*0)*mux-1:0] mem4[0:3];  
|---reg [(word_width+r_col*0)*mux-1:0] mem5[0:3];  
|---reg [(word_width+r_col*0)*mux-1:0] mem6[0:3];  
|---reg [(word_width+r_col*0)*mux-1:0] mem7[0:3];  
|---reg [(word_width+r_col*0)*mux-1:0] mem8[0:3];  
|---reg [(word_width+r_col*0)*mux-1:0] mem9[0:3];  
|---reg [(word_width+r_col*0)*mux-1:0] mem10[0:3];  
|---reg [(word_width+r_col*0)*mux-1:0] mem11[0:3];  
|---reg [(word_width+r_col*0)*mux-1:0] mem12[0:3];  
|---reg [(word_width+r_col*0)*mux-1:0] mem13[0:3];  
|---reg [(word_width+r_col*0)*mux-1:0] mem14[0:3];  
|---reg [(word_width+r_col*0)*mux-1:0] mem15[0:3];
```

- New MRAM Bit-cell and Array modeling

```
|---// TYPEDEF  
|---typedef struct packed {  
|---|---logic data;  
|---|---bit [9:0] refl_voltage;  
|---|---bit [9:0] ref0_voltage;  
|---} mbit;
```

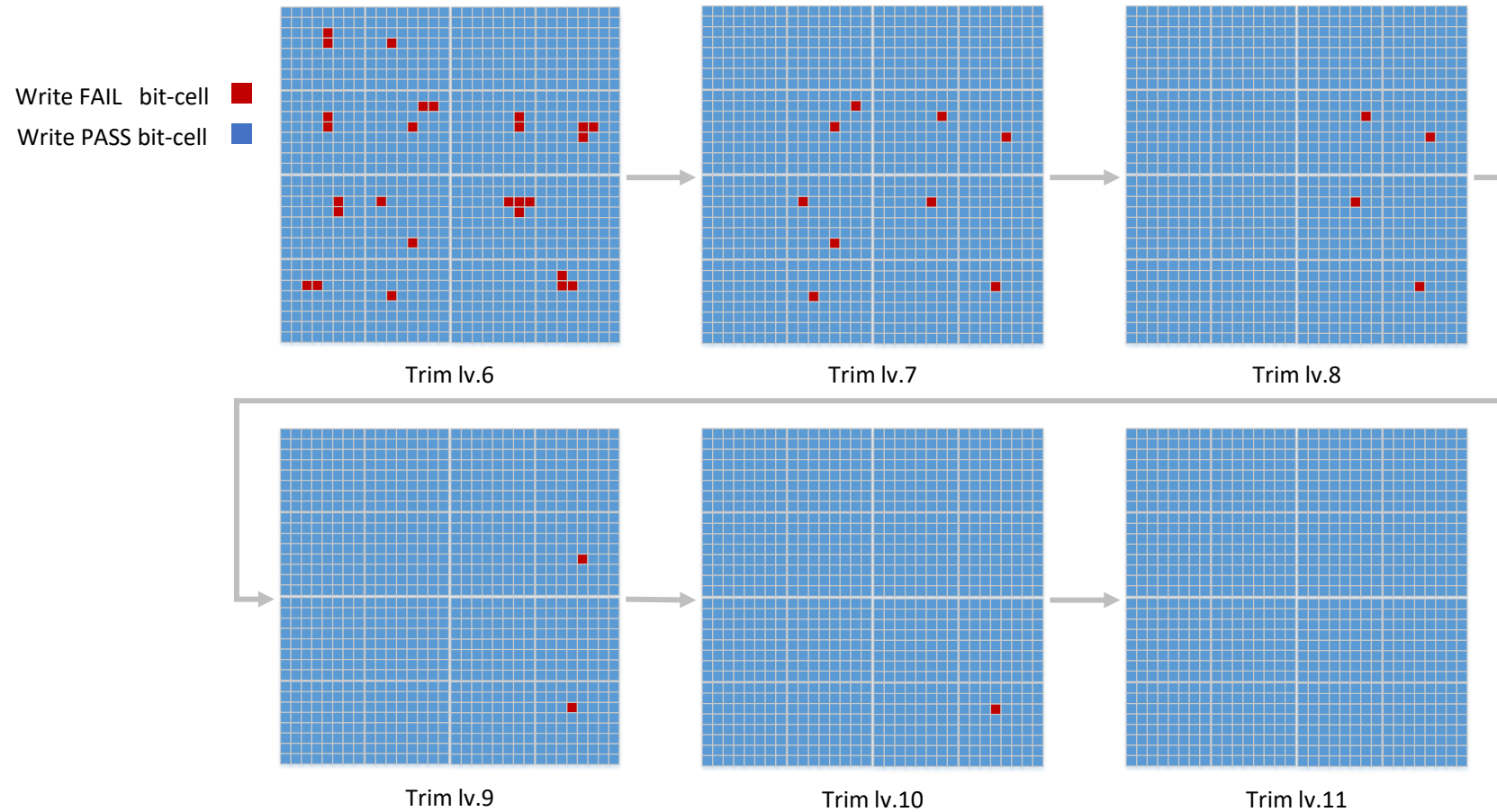
```
|---// Memory definition-  
|---mbit [(word_width+r_col*0)*mux-1:0] mem[0:4095];  
|---mbit [(word_width+r_col*0)*mux-1:0] mem0[0:3];  
|---mbit [(word_width+r_col*0)*mux-1:0] mem1[0:3];  
|---mbit [(word_width+r_col*0)*mux-1:0] mem2[0:3];  
|---mbit [(word_width+r_col*0)*mux-1:0] mem3[0:3];  
|---mbit [(word_width+r_col*0)*mux-1:0] mem4[0:3];  
|---mbit [(word_width+r_col*0)*mux-1:0] mem5[0:3];  
|---mbit [(word_width+r_col*0)*mux-1:0] mem6[0:3];  
|---mbit [(word_width+r_col*0)*mux-1:0] mem7[0:3];  
|---mbit [(word_width+r_col*0)*mux-1:0] mem8[0:3];  
|---mbit [(word_width+r_col*0)*mux-1:0] mem9[0:3];  
|---mbit [(word_width+r_col*0)*mux-1:0] mem10[0:3];  
|---mbit [(word_width+r_col*0)*mux-1:0] mem11[0:3];  
|---mbit [(word_width+r_col*0)*mux-1:0] mem12[0:3];  
|---mbit [(word_width+r_col*0)*mux-1:0] mem13[0:3];  
|---mbit [(word_width+r_col*0)*mux-1:0] mem14[0:3];  
|---mbit [(word_width+r_col*0)*mux-1:0] mem15[0:3];
```


Ref_voltage profile setting

```
//=====
// bitcell ref_voltage setting
//=====
task set_ref_voltage;
---static int seed = 777;
---int ref_value;
---for(int i=0; i<WORDS/mux; i=i+1) begin
---  ---for(j=0; j< (word_width+0)*mux; j=j+1) begin
---    ---ref_value = $dist_normal(seed, _____);
---    ---mem[i][j].ref0_voltage = ref_value-_____ < 0 ? 0 : ref_value-_____;
---    ---ref0_voltage[mem[i][j].ref0_voltage] +=1;
---    ---ref_value = $dist_normal(seed, _____);
---    ---mem[i][j].ref1_voltage = ref_value-_____ < 0 ? 0 : ref_value-_____;
---    ---ref1_voltage[mem[i][j].ref1_voltage] +=1;
---    ---//$display("ref_voltage : %d", mem[i][j].ref_voltage);
---  ---end
---end
---for(int i=0; i<4; i=i+1) begin
---  ---for(int j=0; j< (word_width+0)*mux; j=j+1) begin
---    ---ref_value = $dist_normal(seed, _____);
---    ---mem0[i][j].ref0_voltage = ref_value-_____ < 0 ? 0 : ref_value-_____;
---    ---ref0_voltage[mem0[i][j].ref0_voltage] +=1;
---    ---ref_value = $dist_normal(seed, _____);
---    ---mem0[i][j].ref1_voltage = ref_value-_____ < 0 ? 0 : ref_value-_____;
---    ---ref1_voltage[mem0[i][j].ref1_voltage] +=1;
---    ---//$display("ref_voltage : %d", mem[i][j].ref_voltage);
---  ---end
---end
```

```
//=====
// mbit ref-voltage aware Write Task
//=====
function reg mbit_write(mbit bit_cell, reg write_data);
---integer trim_voltage;
---if ( `WVAT_MODE != 2 ) begin
---  ---ReportMessage(DEBUG, $sformatf("trim_voltage: %dmV", trim_voltage));
---  ---if ( write_data == 1'b0 ) begin
---    ---if ( write0_trim_en == 1'b1 ) begin
---      ---trim_voltage = _____+write0_trim_____
---      ---ReportMessage(DEBUG, $sformatf("cell_voltage: %dmV", _____+bit_cell.ref0_voltage));
---      ---if ( _____+bit_cell.ref0_voltage > trim_voltage ) begin
---        ---if ( `WVAT_MODE == 0 ) begin
---          ---return bit_cell.data;
---        ---end
---      ---else if ( `WVAT_MODE == 1 ) begin
---        ---return 1'b1;
---      ---end
---    ---end
---  ---end
---  ---else if ( write_data == 1'b1 ) begin
---    ---if ( writel_trim_en == 1'b1 ) begin
---      ---trim_voltage = _____+write0_trim_____+writel_trim_____
---      ---ReportMessage(DEBUG, $sformatf("cell_voltage: %dmV", _____+bit_cell.ref1_voltage));
---      ---if ( _____+bit_cell.ref1_voltage > trim_voltage ) begin
---        ---if ( `WVAT_MODE == 0 ) begin
---          ---return bit_cell.data;
---        ---end
---      ---else if ( `WVAT_MODE == 1 ) begin
---        ---return 1'b0;
---      ---end
---    ---end
---  ---end
---end
---end
---return write_data;
endfunction
```

Cell Level Variation aware Simulation diagram



Simulation Result

```
481942 --- 27308476000 : PASS : DOUT == [00000000000000000000]
481943 --- 27308646000 : [READ TEST ADD : 27359]
481944 --- 27308646000 : ERROR : EXPECT == [00000000000000000000]
481945 --- 27308646000 : ERROR : DOUT == [00000000000000000000]
481946 --- 27308816000 : [READ TEST ADD : 2735a]
481947 --- 27308816000 : PASS : EXPECT == [00000000000000000000]
481948 --- 27308816000 : PASS : DOUT == [00000000000000000000]
481949 --- 27308986000 : [READ TEST ADD : 2735b]
481950 --- 27308986000 : PASS : EXPECT == [00000000000000000000]
481951 --- 27308986000 : PASS : DOUT == [00000000000000000000]
481952 +-34495 Lines: 27309156000 : [READ TEST ADD : 2735c]-----+
516447 --- 29263816000 : PASS : EXPECT == [00000000000000000000]
516448 --- 29263816000 : PASS : DOUT == [00000000000000000000]
516449 --- 29263986000 : [READ TEST ADD : 2a047]
516450 --- 29263986000 : PASS : EXPECT == [00000000000000000000]
516451 --- 29263986000 : PASS : DOUT == [00000000000000000000]
516452 --- 29264156000 : [READ TEST ADD : 2a048]
516453 --- 29264156000 : ERROR : EXPECT == [00000000000000000000]
516454 --- 29264156000 : ERROR : DOUT == [00000000000000000000]
516455 --- 29264326000 : [READ TEST ADD : 2a049]
516456 --- 29264326000 : PASS : EXPECT == [00000000000000000000]
516457 --- 29264326000 : PASS : DOUT == [00000000000000000000]
516458 --- 29264496000 : [READ TEST ADD : 2a04a]
516459 --- 29264496000 : PASS : EXPECT == [00000000000000000000]
516460 --- 29264496000 : PASS : DOUT == [00000000000000000000]
516461 +-79495 Lines: 29264666000 : [READ TEST ADD : 2a04b]-----+
595956 --- 33769326000 : PASS : EXPECT == [00000000000000000000]
595957 --- 33769326000 : PASS : DOUT == [00000000000000000000]
595958 --- 33769496000 : [READ TEST ADD : 307ce]
595959 --- 33769496000 : PASS : EXPECT == [00000000000000000000]
595960 --- 33769496000 : PASS : DOUT == [00000000000000000000]
595961 --- 33769666000 : [READ TEST ADD : 307cf]
595962 --- 33769666000 : ERROR : EXPECT == [00000000000000000000]
595963 --- 33769666000 : ERROR : DOUT == [00000000000000000000]
595964 --- 33769836000 : [READ TEST ADD : 307d0]
595965 --- 33769836000 : PASS : EXPECT == [00000000000000000000]
595966 --- 33769836000 : PASS : DOUT == [00000000000000000000]
595967 --- 33770006000 : [READ TEST ADD : 307d1]
595968 --- 33770006000 : PASS : EXPECT == [00000000000000000000]
595969 --- 33770006000 : PASS : DOUT == [00000000000000000000]
595970 +-35473 Lines: 33770176000 : [READ TEST ADD : 307d2]-----+
631443 --- 35780256000 : PASS : EXPECT == [00000000000000000000]
631444 --- 35780256000 : PASS : DOUT == [00000000000000000000]
631445 --- 35780256000 : PASS : EXPECT == [00000000000000000000]
631446 --- 35780256000 : PASS : DOUT == [00000000000000000000]
631447 --- 35780256000 : PASS : EXPECT == [00000000000000000000]
631448 --- 35780256000 : PASS : DOUT == [00000000000000000000]
631449 --- 35780256000 : PASS : EXPECT == [00000000000000000000]
631450 --- 35780256000 : PASS : DOUT == [00000000000000000000]
```

Trim_9

Trim_10

Trim_11

Summary

- To support MRAM probabilistic write, we use user define data type for MRAM memory array.
- Our modeling enables simulation base design verification for DNA & BIST RTL.
- Our modeling support to develop BIST algorithm for Samsung Foundry's MRAM.

Questions

- Contact : sanggi.do@samsung.com